

# WPT2N41

Single, PNP, -30V, -3A, Power Transistor

## Descriptions

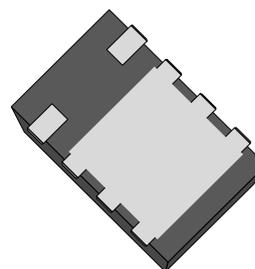
The WPT2N41 is PNP bipolar power transistor with very low saturation voltage. This device is suitable for use in charging circuit and other power management. Standard Product WPT2N41 is Pb-free.

## Features

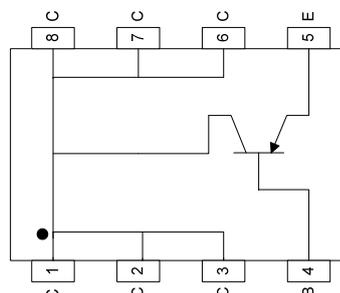
- Ultra low collector-to-emitter saturation voltage
- High DC current gain >100
- 3A continue collector current
- Small package PDFN3x2-8L.

## Applications

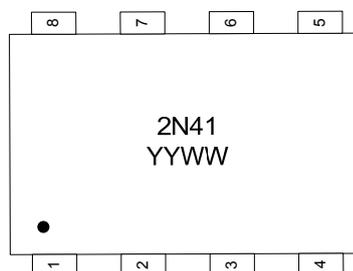
- Charging circuit
- Power regulator
- Other power management in portable equipments



PDFN3x2-8L



Pin configuration (Top view)



2N41 = Device code

YY = Year

WW = Week

Marking

## Order information

Device	Package	Shipping
WPT2N41-8/TR	PDFN3x2-8L	3000/Reel&Tape

**Absolute maximum ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	-32	V
Collector-base voltage	$V_{CBO}$	-45	V
Emitter-base voltage	$V_{EBO}$	-6	V
Continues collector current <sup>a</sup>	$I_C$	-3	A
Continues collector current <sup>b</sup>		-2	A
Pulse collector current <sup>c</sup>	$I_{CM}$	-6	A
Power dissipation <sup>a</sup>	$P_D$	3.0	W
Power dissipation <sup>b</sup>		1.2	W
Junction Temperature	$T_J$	150	°C
Lead Temperature	$T_L$	260	°C
Storage Temperature Range	$T_{stg}$	-55~155	°C

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

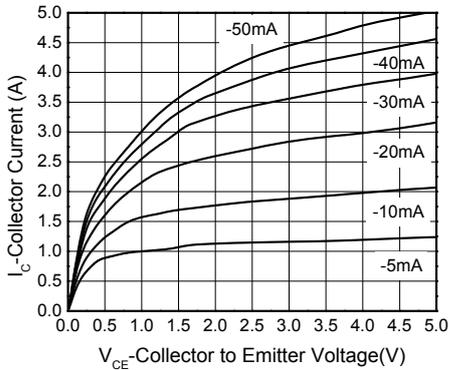
b Surface mounted on FR-4 board using minimum pad size, 1oz copper

c Pulse width=300μs, Duty Cycle<2%

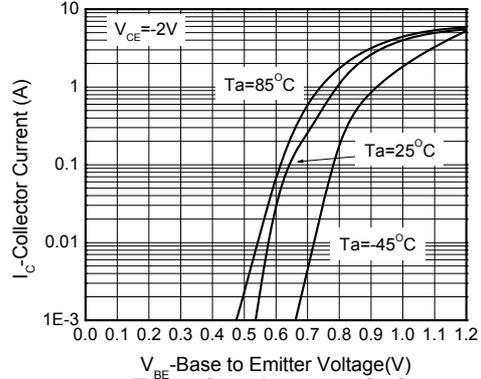
**Electronics Characteristics (Ta=25°C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage	$BV_{CEO}$	$I_C=-10mA, I_B=0mA$	-32			V
Collector-base breakdown voltage	$BV_{CBO}$	$I_C=-1mA, I_E=0mA$	-45			V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E=-100uA, I_C=0mA$	-6			V
Collector cutoff current	$I_{CBO}$	$V_{CB}=-40V$			-100	nA
Emitter cutoff current	$I_{EBO}$	$V_{EB}=-5V$			-100	nA
Collector-emitter saturation voltage <sup>c</sup>	$V_{CE(sat)}$	$I_C=-2A, I_B=-200mA$		-0.2	-0.5	V
Base-emitter saturation voltage <sup>c</sup>	$V_{BE(sat)}$	$I_C=-2A, I_B=-200mA$		-1.0	-1.5	V
DC current gain <sup>c</sup>	$h_{FE}$	$I_C=-1A, V_{CE}=-2V$	100	200	320	

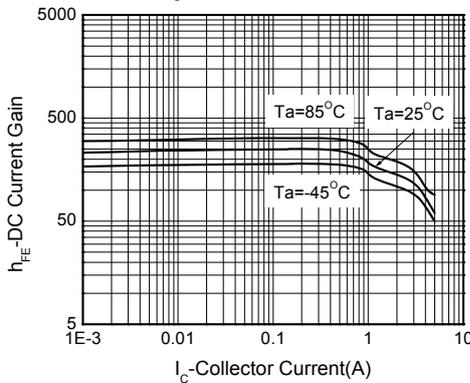
Typical Characteristics (Ta=25°C, unless otherwise noted)



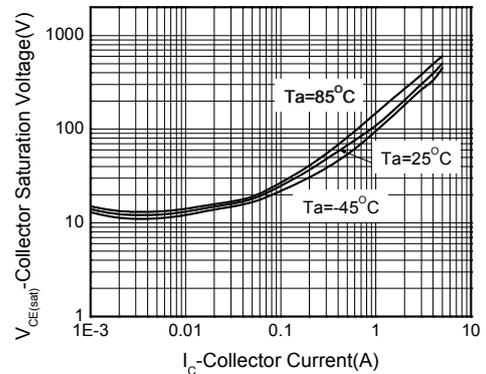
Output characteristics



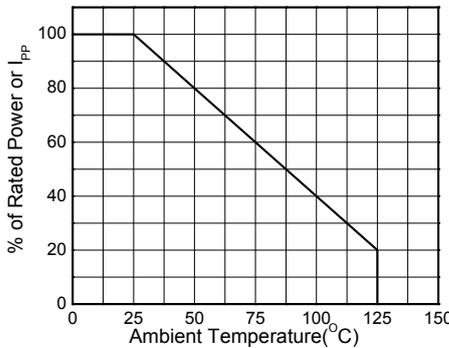
Transfer characteristics



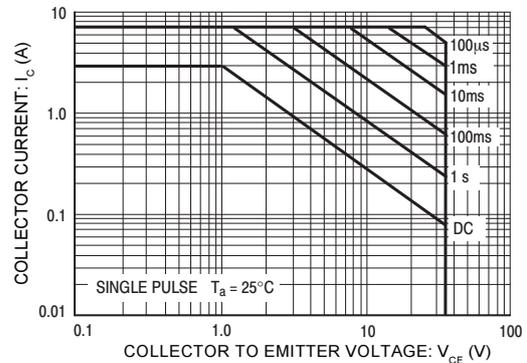
DC current gain



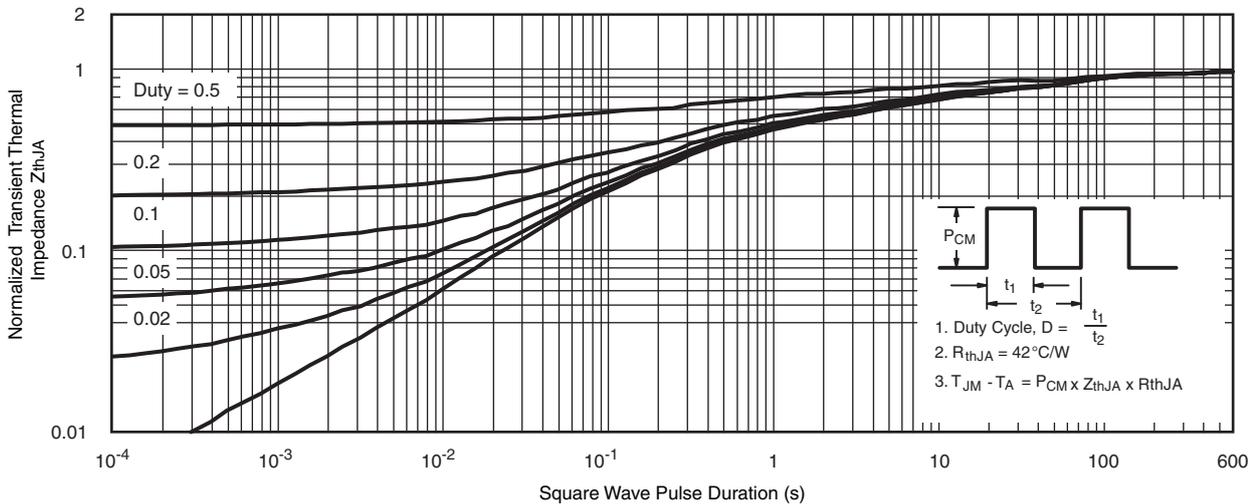
C-E saturation voltage vs. Collector current



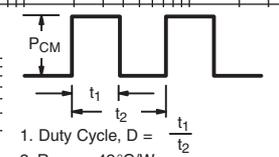
Power Derating



Safe operating area



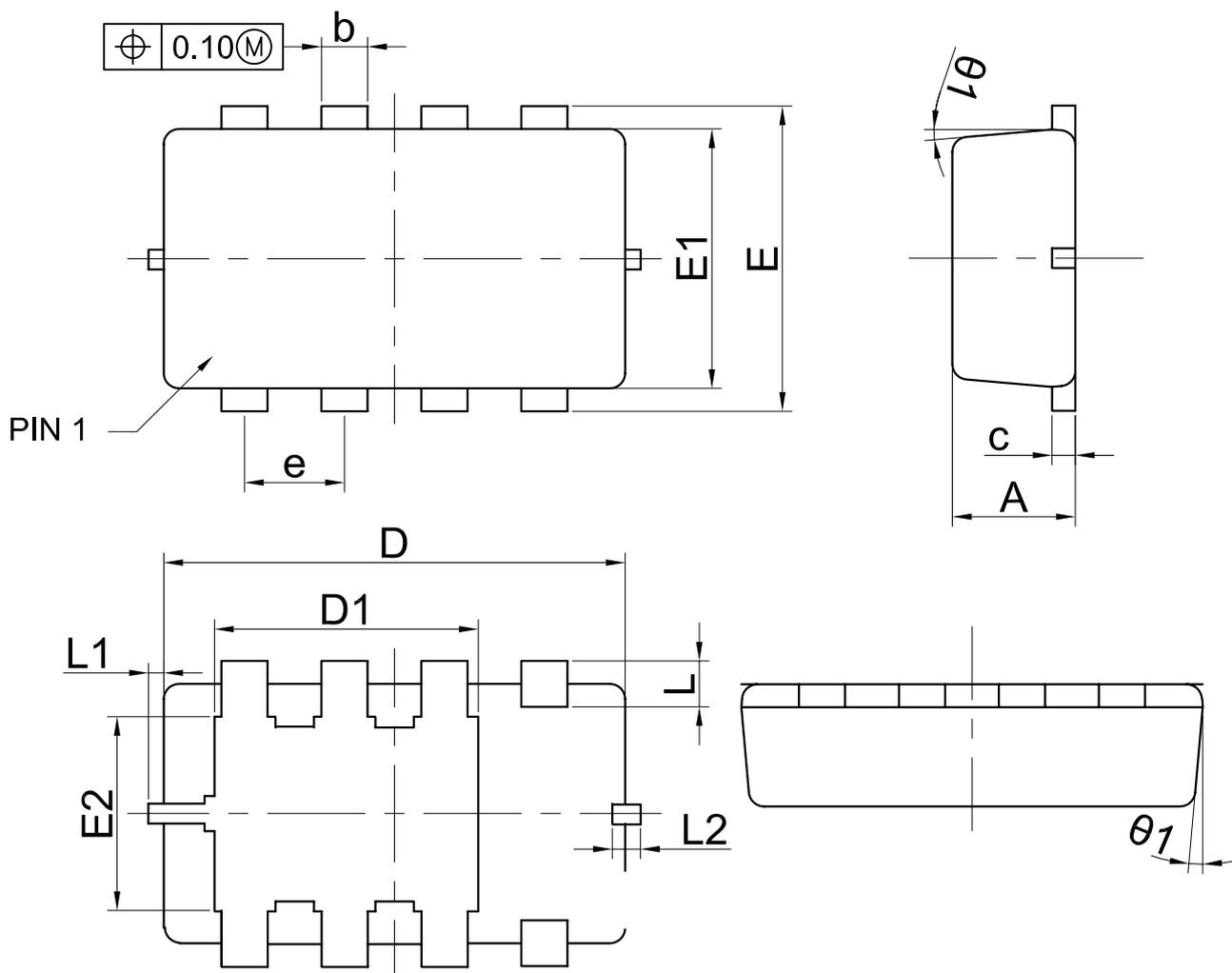
Transient thermal response (Junction-to-Ambient)



- Duty Cycle,  $D = \frac{t_1}{t_2}$
- $R_{thJA} = 42^\circ\text{C/W}$
- $T_{JM} - T_A = P_{CM} \times Z_{thJA} \times R_{thJA}$

Package outline dimensions

PDFN3x2-8L



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.24	0.30	0.35
c	0.08	0.15	0.20
D	2.90	3.00	3.05
D1	1.52	1.62	1.72
E	1.90	2.00	2.10
E1	1.60	1.70	1.75
E2	1.07	1.17	1.27
e	0.65 BSC		
L	0.20	0.30	0.40
L1	0.00	—	0.10
L2	0.184MAX		
$\theta_1$	0°	5°	8°